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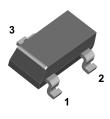


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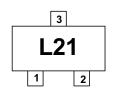
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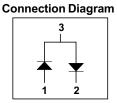


BAS31 Small Signal Diode



SOT-23





Ordering Information

| Part Number | Top Mark | Package | Packing Method |
|-------------|----------|-----------|--|
| BAS31 | L21 | SOT-23 3L | Tape and Reel, 7 inch Reel, 3000 pcs |
| BAS31-D87Z | L21 | SOT-23 3L | Tape and Reel, 13 inch Reel, 10000 pcs |

Absolute Maximum Ratings(1), (2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}\text{C}$ unless otherwise noted.

| Symbol | Parameter | | Value | Unit |
|--------------------|--|-------------------------------|-------------|------|
| V_{RRM} | Maximum Repetitive Reverse Voltage | | 120 | V |
| I _{F(AV)} | Average Rectified Forward Current | | 200 | mA |
| I _{FSM} | Non-Repetitive Peak Forward Surge Current | Pulse Width = 1.0 second | 1.0 | А |
| | | Pulse Width = 1.0 microsecond | 2.0 | |
| T _{STG} | Storage Temperature Range | | -55 to +150 | °C |
| T _J | Operating Junction Temperature | 3 | 150 | °C |

Notes:

- 1. These ratings are based on a maximum junction temperature of 150 $^{\circ}\text{C}.$
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

| Symbol | Parameter | Value | Unit |
|-----------------|---|-------|------|
| P_{D} | Power Dissipation | 350 | mW |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | 357 | °C/W |

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

| Symbol | Parameter | Conditions | Min. | Max. | Unit |
|-----------------|-----------------------|---|------|------|------|
| V _R | Breakdown Voltage | I _R = 1.0 mA | 120 | | V |
| | Forward Voltage | I _F = 10 mA | | 750 | mV |
| V _F | | I _F = 50 mA | | 840 | mV |
| | | I _F = 100 mA | | 900 | mV |
| | | I _F = 200 mA | | 1.00 | V |
| | | I _F = 400 mA | | 1.25 | V |
| I _R | Reverse Current | V _R = 90 V | | 100 | nA |
| | | V _R = 90 V, T _A = 150°C | | 100 | μΑ |
| C _T | Total Capacitance | V _R = 0, f = 1.0 MHz | | 35 | pF |
| t _{rr} | Reverse Recovery Time | $I_F = I_R = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA},$ $R_L = 100 \Omega$ | | 50 | ns |

Typical Performance Characteristics

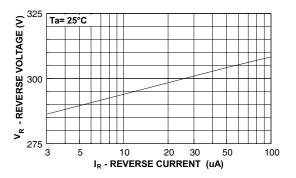


Figure 1. Reverse Voltage vs. Reverse Current BV - 1.0 to 100 μA

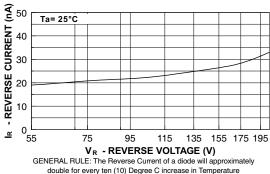


Figure 2. Reverse Current vs. Reverse Voltage I_R - 55 to 205 V

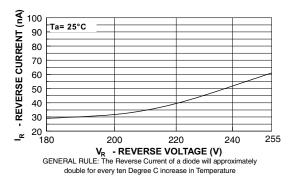


Figure 3. Reverse Current vs. Reverse Voltage I_R - 180 to 255 V

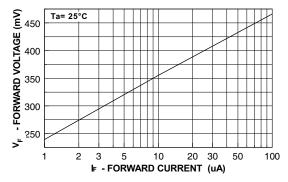


Figure 4. Forward Voltage vs. Forward Current V_F - 1.0 to 100 μA

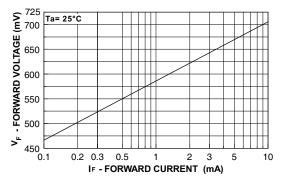


Figure 5. Forward Voltage vs. Forward Current V_F - 0.1 to 10 mA

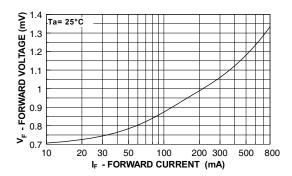


Figure 6. Forward Voltage vs. Forward Current V_F - 10 to 800 mA

Typical Performance Characteristics (Continued)

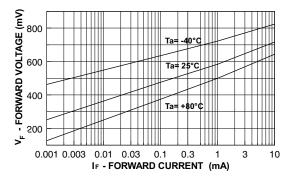


Figure 7. Forward Voltage vs. Ambient Temperature V_F - 1.0 μA - 10 mA (- 40 to +80°C)

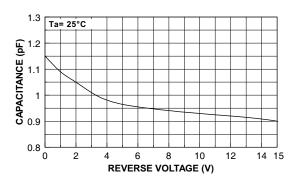


Figure 8. Capacitance vs. Reverse Voltage

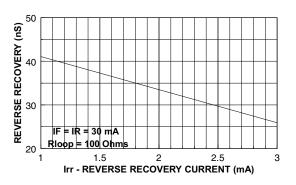


Figure 9. Reverse Recovery Time vs. Reverse Recovery Current (Irr)

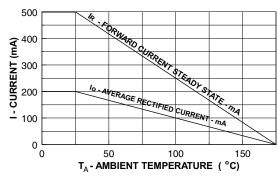


Figure 10. Average Rectified Current(I_O) and Forward Current (I_F) vs. Ambient Temperature(T_A)

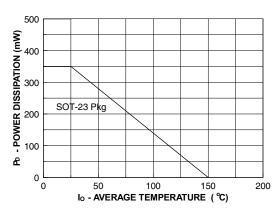


Figure 11. Power Derating Curve

Physical Dimensions 0.95 2.92±0.20 3 1.40 1.30^{+0.20}_{-0.15} 2.20 2 0.60 0.37 (0.29) -0.95 ⊕ 0.20M A B | 1.00 1.90 1.90 LAND PATTERN RECOMMENDATION SEE DETAIL A 1.20 MAX 0.10 (0.93)0.00 ○ 0.10 M C С 2.40±0.30 NOTES: UNLESS OTHERWISE SPECIFIED **GAGE PLANE** A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H. B) ALL DIMENSIONS ARE IN MILLIMETERS. 0.23 0.08 C) DIMENSIONS ARE INCLUSIVE OF BURRS. 0.25 MOLD FLASH AND TIE BAR EXTRUSIONS. D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994. 0.20 MIN SEATING E) DRAWING FILE NAME: MA03DREV10 **PLANE** (0.55)**DETAIL A** SCALE: 2X

Figure 12. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE

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